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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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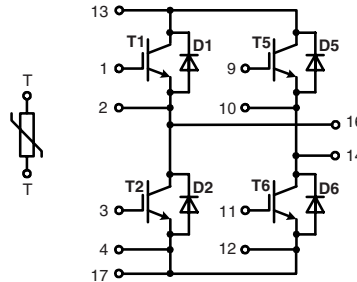
IGBT Modules

H-Bridge

Short Circuit SOA Capability
 Square RBSOA

$I_{C25} = 90 \text{ A}$
 $V_{CES} = 600 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.1 \text{ V}$

Type:	NTC - Option:
MKI 75-06 A7	without NTC
MKI 75-06 A7T	with NTC



IGBTs		
Symbol	Conditions	Maximum Ratings
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600 V
V_{GES}		± 20 V
I_{C25}	$T_C = 25^{\circ}\text{C}$	90 A
I_{C80}	$T_C = 80^{\circ}\text{C}$	60 A
RBSOA	$V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega; T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 120$ $V_{CEK} \leq V_{CES}$ A
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10 μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	280 W

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate
- UL registered, E 72873

Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

Typical Applications

- motor control
 - DC motor armature winding
 - DC motor excitation winding
 - synchronous motor excitation winding
- supply of transformer primary winding
 - power supplies
 - welding
 - X-ray
 - UPS
 - battery charger

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.1	2.6	V
$V_{GE(th)}$	$I_C = 1.5 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.9	1.3	mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$		200	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 75 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 18 \Omega$		50	ns
			50	ns
			270	ns
			40	ns
			3.5	mJ
			2.5	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$	3200		pF
Q_{Gon}	$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 75 \text{ A}$	190		nC
R_{thJC}	(per IGBT)		0.44	K/W

IXYS reserves the right to change limits, test conditions and dimensions.

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	140	A
I_{F80}	$T_C = 80^\circ\text{C}$	85	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 75\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.8	2.1	V
I_{RM} t_{rr}	$I_F = 60\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	28		A
		100		ns
R_{thJC}	(per diode)			0.61 K/W

Module

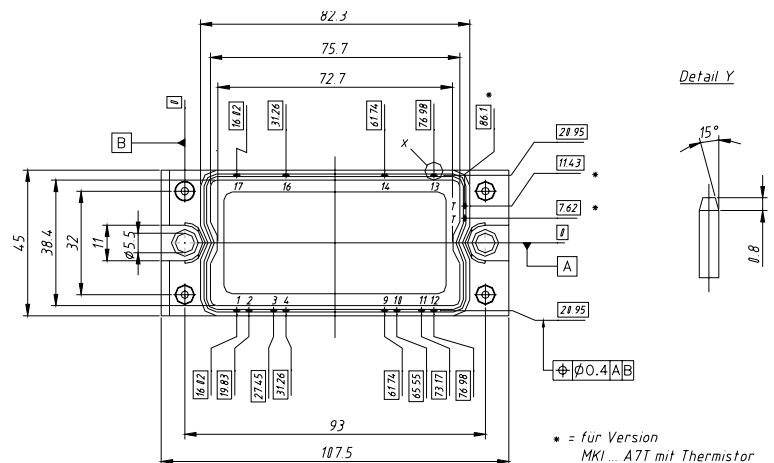
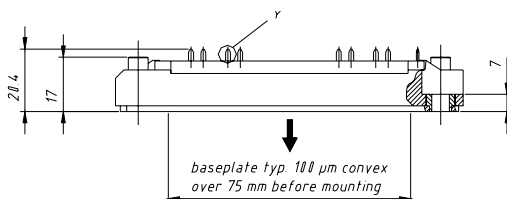
Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			5	m Ω
d_s	Creepage distance on surface	6		mm
d_A	Strike distance in air	6		mm
R_{thCH}	with heatsink compound		0.02	K/W
Weight			180	g

Temperature Sensor NTC

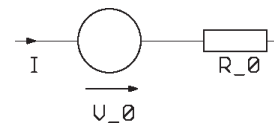
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k Ω
$B_{25/50}$			3375	K

Dimensions in mm (1 mm = 0.0394")



Equivalent Circuits for Simulation

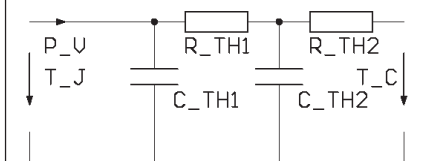
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 0.95\text{ V}; R_0 = 20\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.014\text{ V}; R_0 = 4\text{ m}\Omega$

Thermal Response



IGBT (typ.)
 $C_{th1} = 0.248\text{ J/K}; R_{th1} = 0.343\text{ K/W}$
 $C_{th2} = 1.849\text{ J/K}; R_{th2} = 0.097\text{ K/W}$

Free Wheeling Diode (typ.)
 $C_{th1} = 0.23\text{ J/K}; R_{th1} = 0.483\text{ K/W}$
 $C_{th2} = 1.3\text{ J/K}; R_{th2} = 0.127\text{ K/W}$

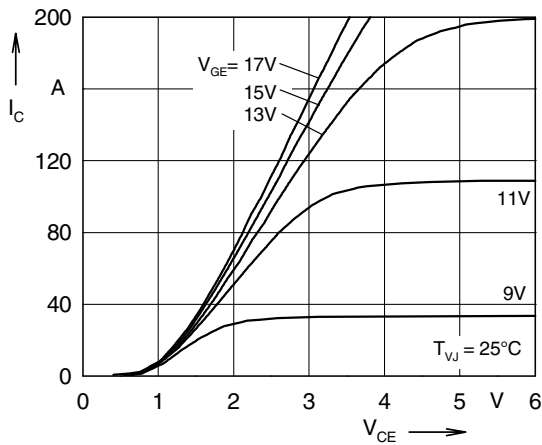


Fig. 1 Typ. output characteristics

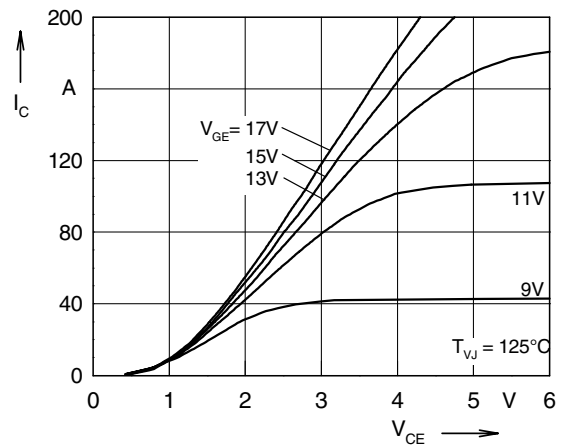


Fig. 2 Typ. output characteristics

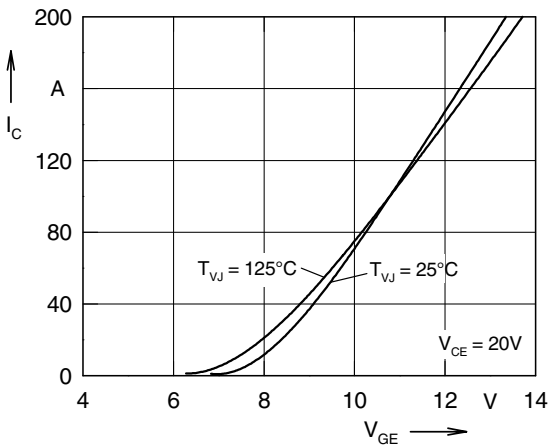


Fig. 3 Typ. transfer characteristics

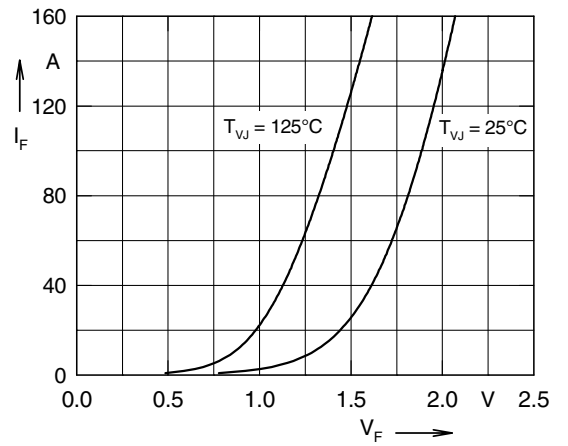


Fig. 4 Typ. forward characteristics of free wheeling diode

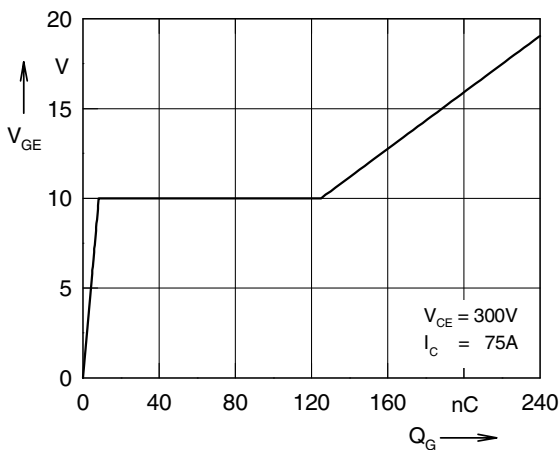


Fig. 5 Typ. turn on gate charge

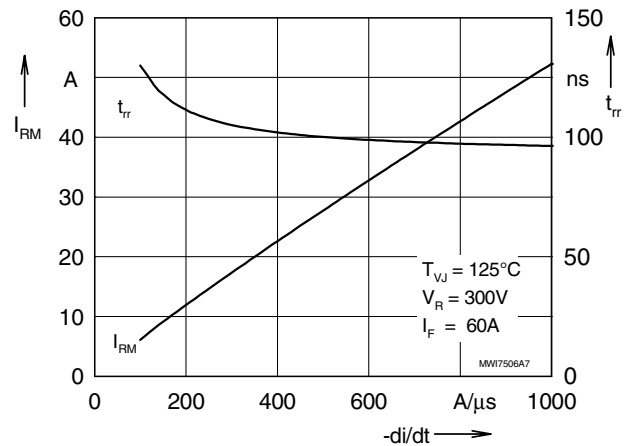


Fig. 6 Typ. turn off characteristics of free wheeling diode

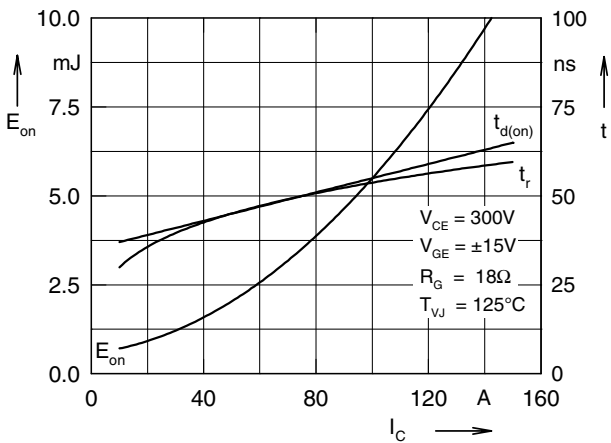


Fig. 7 Typ. turn on energy and switching times versus collector current

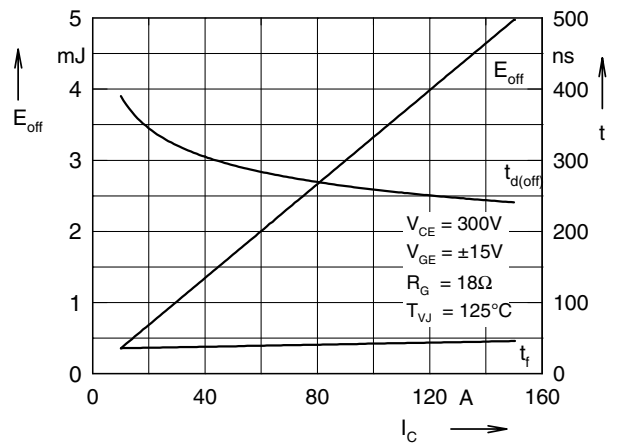


Fig. 8 Typ. turn off energy and switching times versus collector current

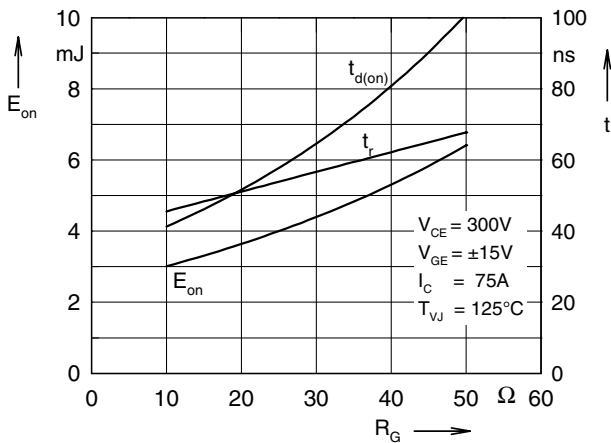


Fig. 9 Typ. turn on energy and switching times versus gate resistor

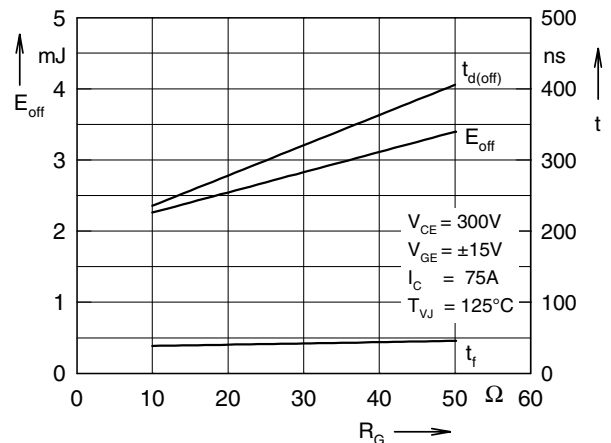


Fig. 10 Typ. turn off energy and switching times versus gate resistor

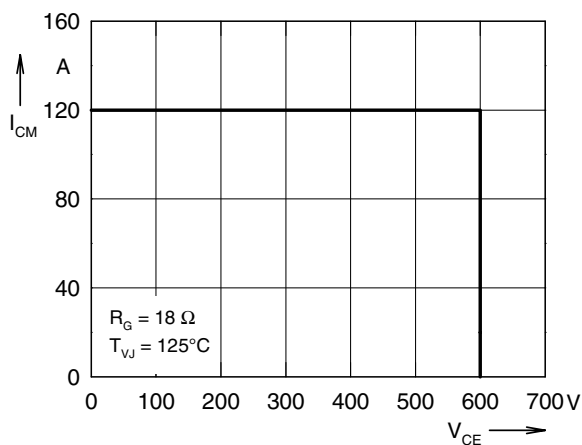


Fig. 11 Reverse biased safe operating area RBSOA

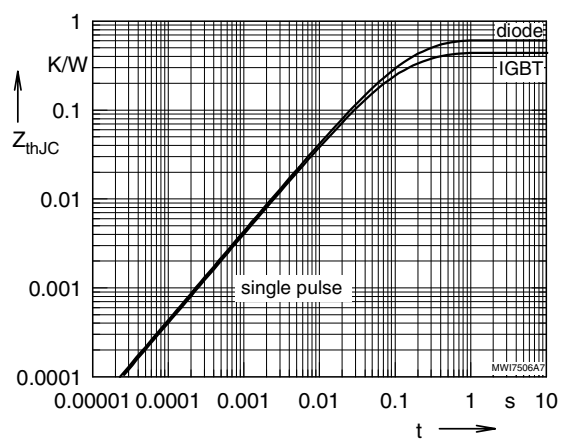


Fig. 12 Typ. transient thermal impedance